



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



DATA SHEET

BUJ106A

Silicon Diffused Power Transistor

Product specification

March 1999



Silicon Diffused Power Transistor

BUJ106A

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in TO220AB envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

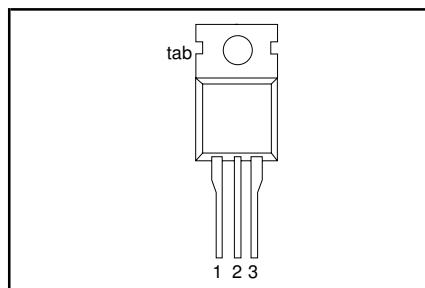
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	700	V
V_{CBO}	Collector-Base voltage (open emitter)		-	700	V
V_{CEO}	Collector-emitter voltage (open base)		-	400	V
I_C	Collector current (DC)		-	10	A
I_{CM}	Collector current peak value		-	20	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	80	W
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 6.0\text{ A}; I_B = 1.2\text{ A}$	0.4	1.0	V
h_{FEsat}		$I_C = 6.0\text{ A}; V_{CE} = 5\text{ V}$	10	15	
t_f	Fall time	$I_C = 5.0\text{ A}; I_{B1} = 1\text{ A}$	20	50	ns

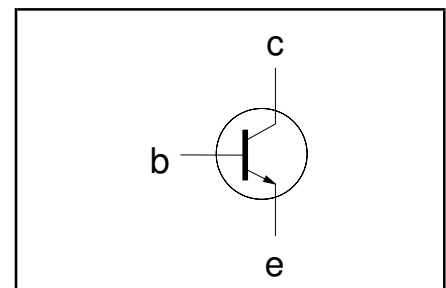
PINNING - TO220AB

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector to emitter voltage	$V_{BE} = 0\text{ V}$	-	700	V
V_{CEO}	Collector to emitter voltage (open base)		-	400	V
V_{CBO}	Collector to base voltage (open emitter)		-	700	V
I_C	Collector current (DC)		-	10	A
I_{CM}	Collector current peak value		-	20	A
I_B	Base current (DC)		-	5	A
I_{BM}	Base current peak value		-	10	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25\text{ °C}$	-	80	W
T_{stg}	Storage temperature		-65	150	°C
T_j	Junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	1.56	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	60	-	K/W

Silicon Diffused Power Transistor

BUJ106A

STATIC CHARACTERISTICS

$T_{mb} = 25\text{ }^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}, I_{CBO} I_{CES}	Collector cut-off current ¹	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^\circ\text{C}$	-	-	0.2 0.5	mA mA
I_{CEO} I_{EBO} $V_{CEOsust}$	Collector cut-off current Emitter cut-off current Collector-emitter sustaining voltage	$V_{CEO} = V_{CEOMmax} (400\text{V})$ $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$	-	-	0.1 1 -	mA mA V
V_{CEsat} V_{BEsat}	Collector-emitter saturation voltage Base-emitter saturation voltage	$I_C = 6.0\text{ A}; I_B = 1.2\text{ A}$ $I_C = 6.0\text{ A}; I_B = 1.2\text{ A}$	-	0.4 1.0	1.0 1.5	V V
h_{FE} h_{FE} h_{FEsat}	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$ $I_C = 6.0\text{ A}; V_{CE} = 5\text{ V}$	10 14 8	17 21 11	32 33 15	

DYNAMIC CHARACTERISTICS

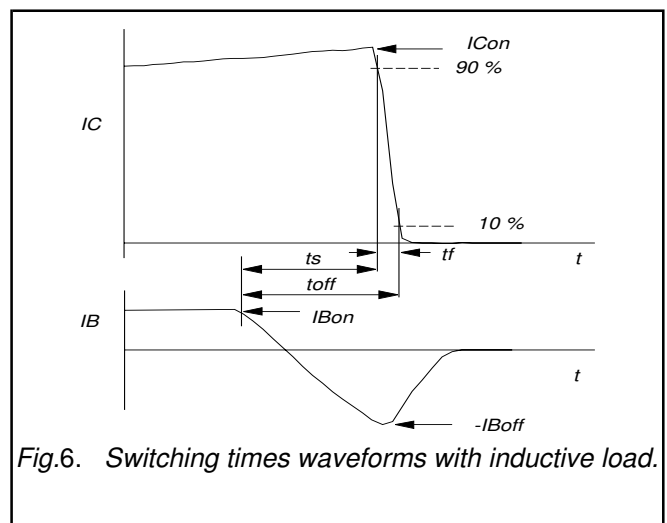
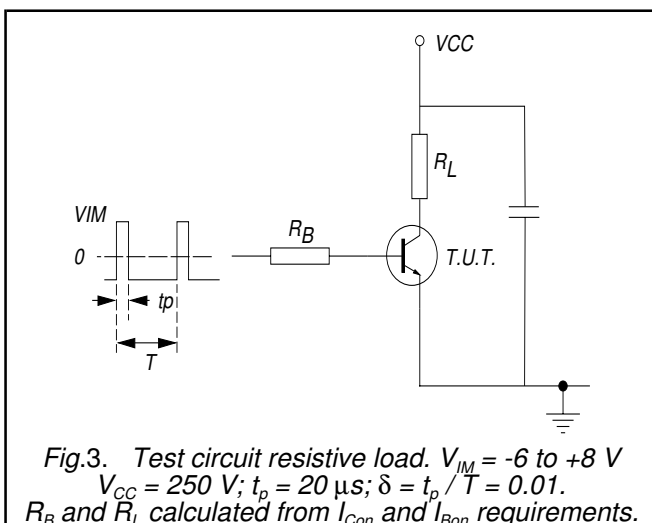
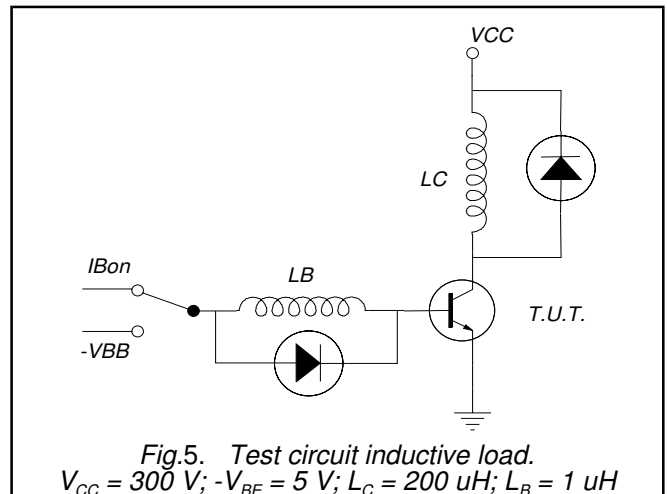
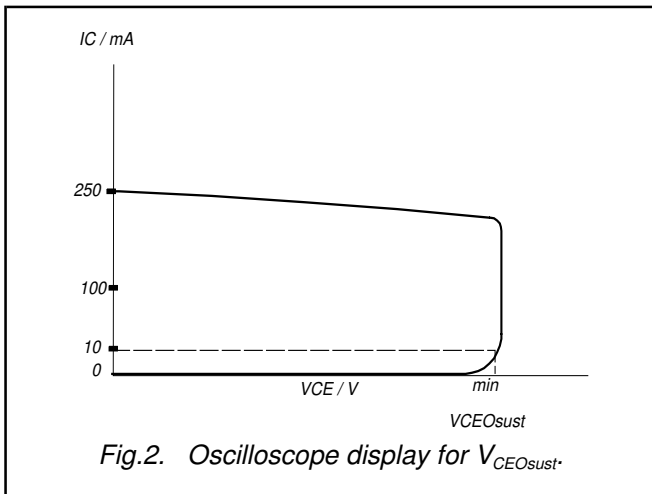
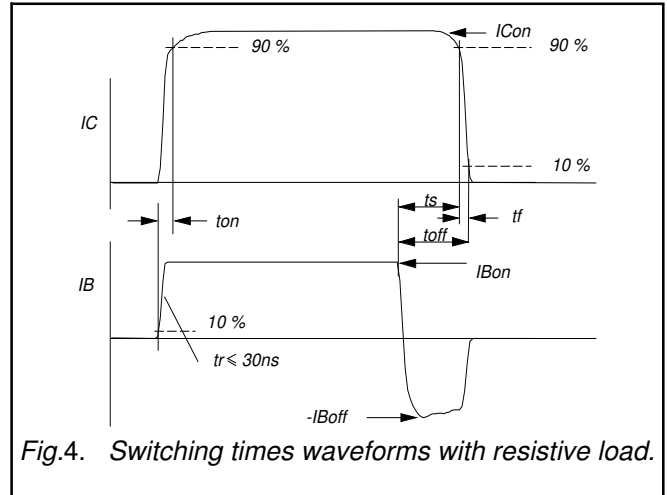
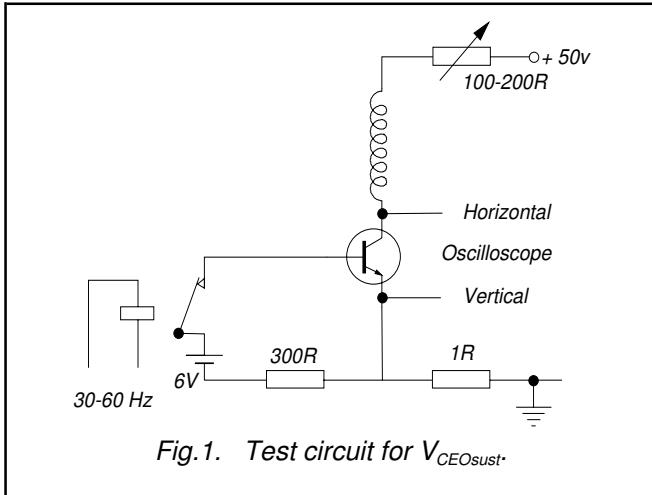
$T_{mb} = 25\text{ }^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
t_{on} t_s t_f	Switching times (resistive load) Turn-on time Turn-off storage time Turn-off fall time	$I_{Con} = 5\text{ A}; I_{Bon} = -I_{Boff} = 1\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$	0.56 2.2 260	0.75 3.3 350	μs μs ns
t_s t_f	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$	1.35 20	1.60 50	μs ns
t_s t_f	Switching times (inductive load) Turn-off storage time Turn-off fall time	$I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^\circ\text{C}$	- -	3.2 100	μs ns

¹ Measured with half sine-wave voltage (curve tracer).

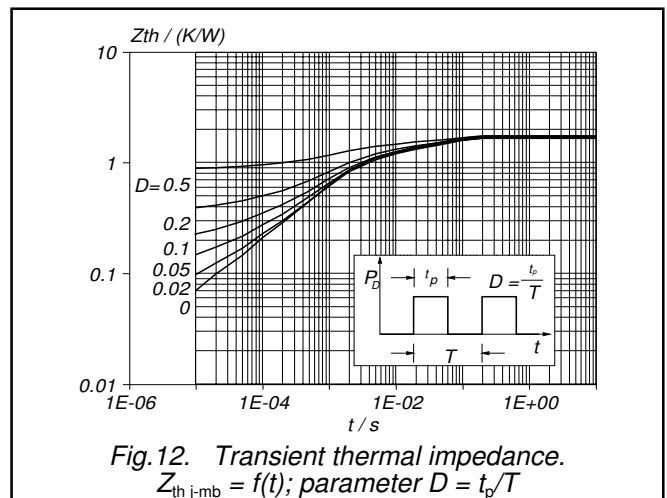
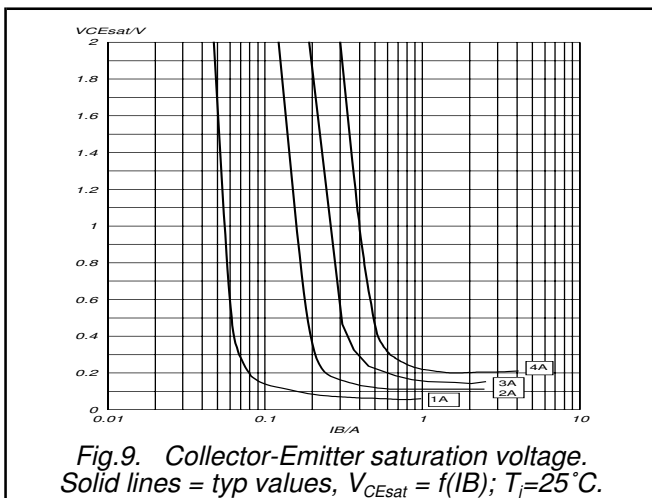
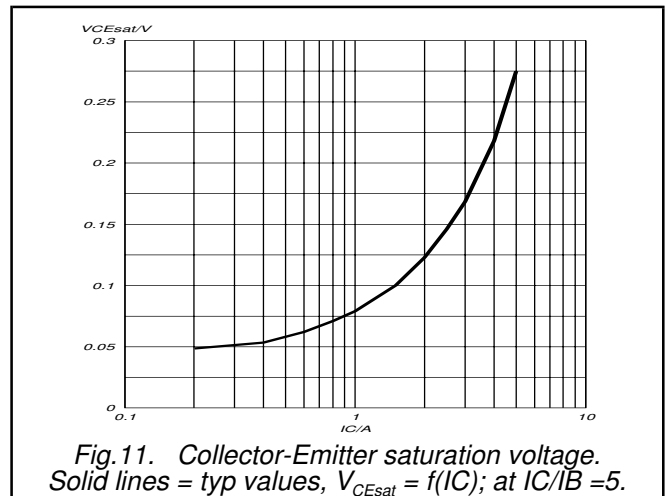
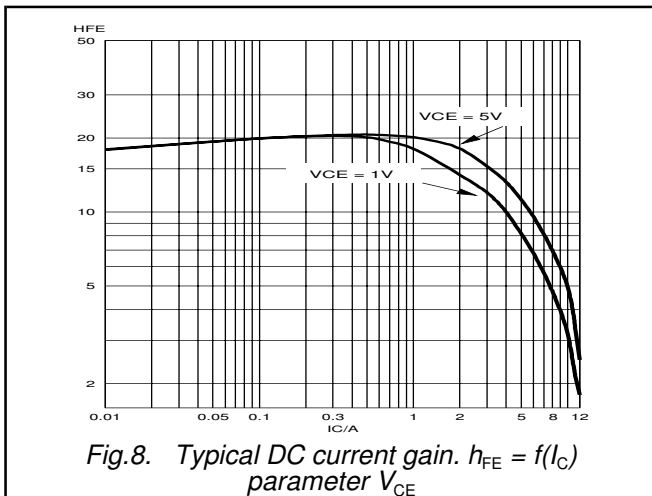
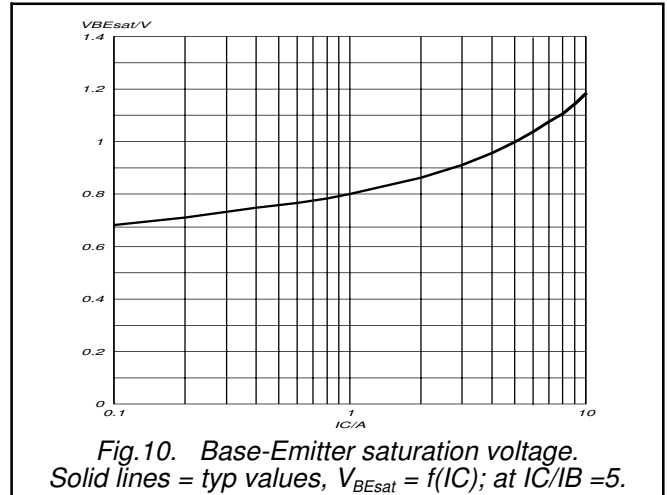
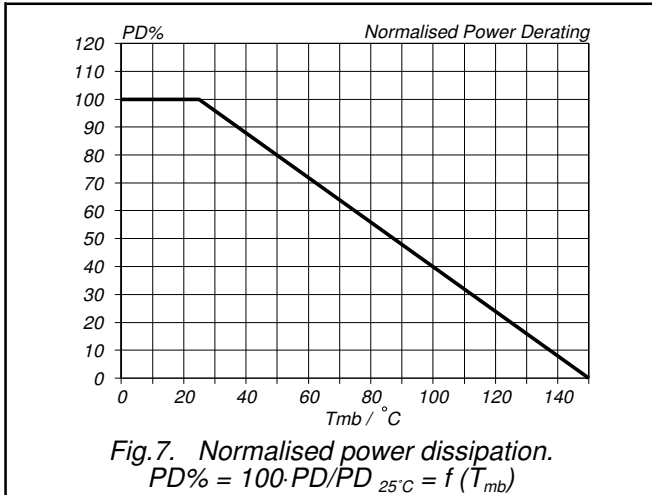
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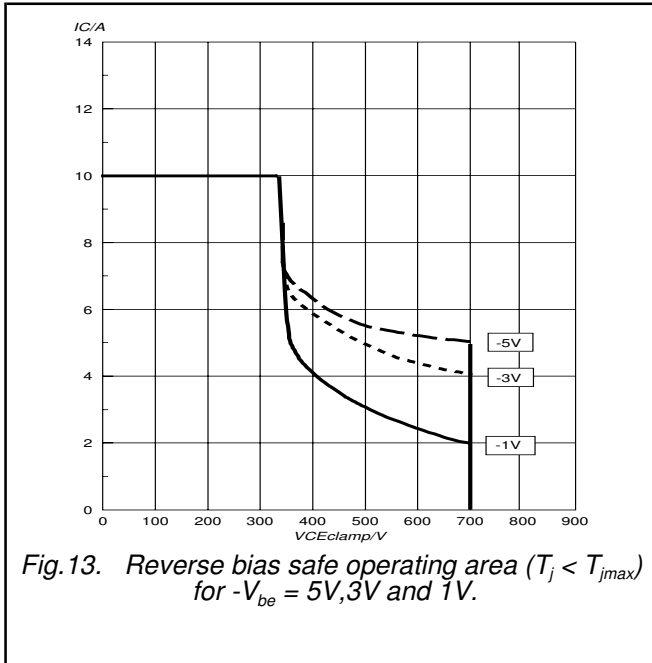


Fig.13. Reverse bias safe operating area ($T_j < T_{jmax}$) for $-V_{be} = 5V, 3V$ and $1V$.

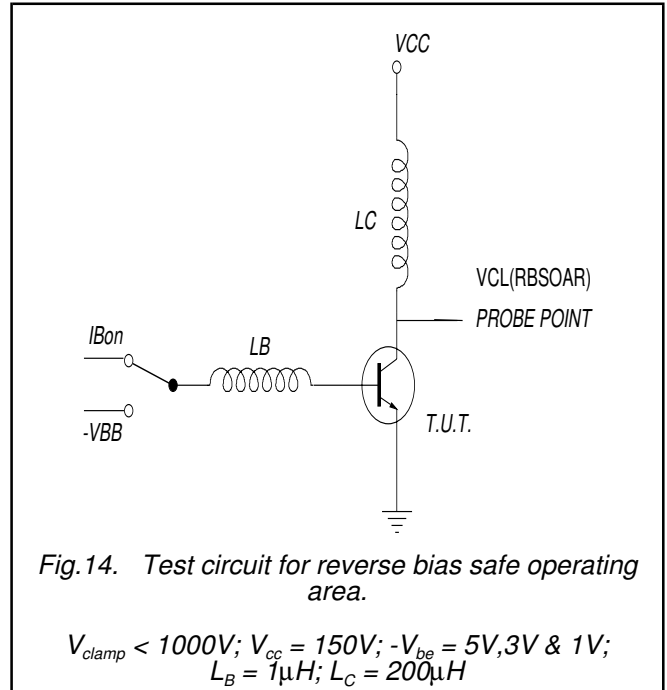


Fig.14. Test circuit for reverse bias safe operating area.

$V_{clamp} < 1000V$; $V_{cc} = 150V$; $-V_{be} = 5V, 3V$ & $1V$;
 $L_B = 1\mu H$; $L_C = 200\mu H$

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BUJ106A

MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

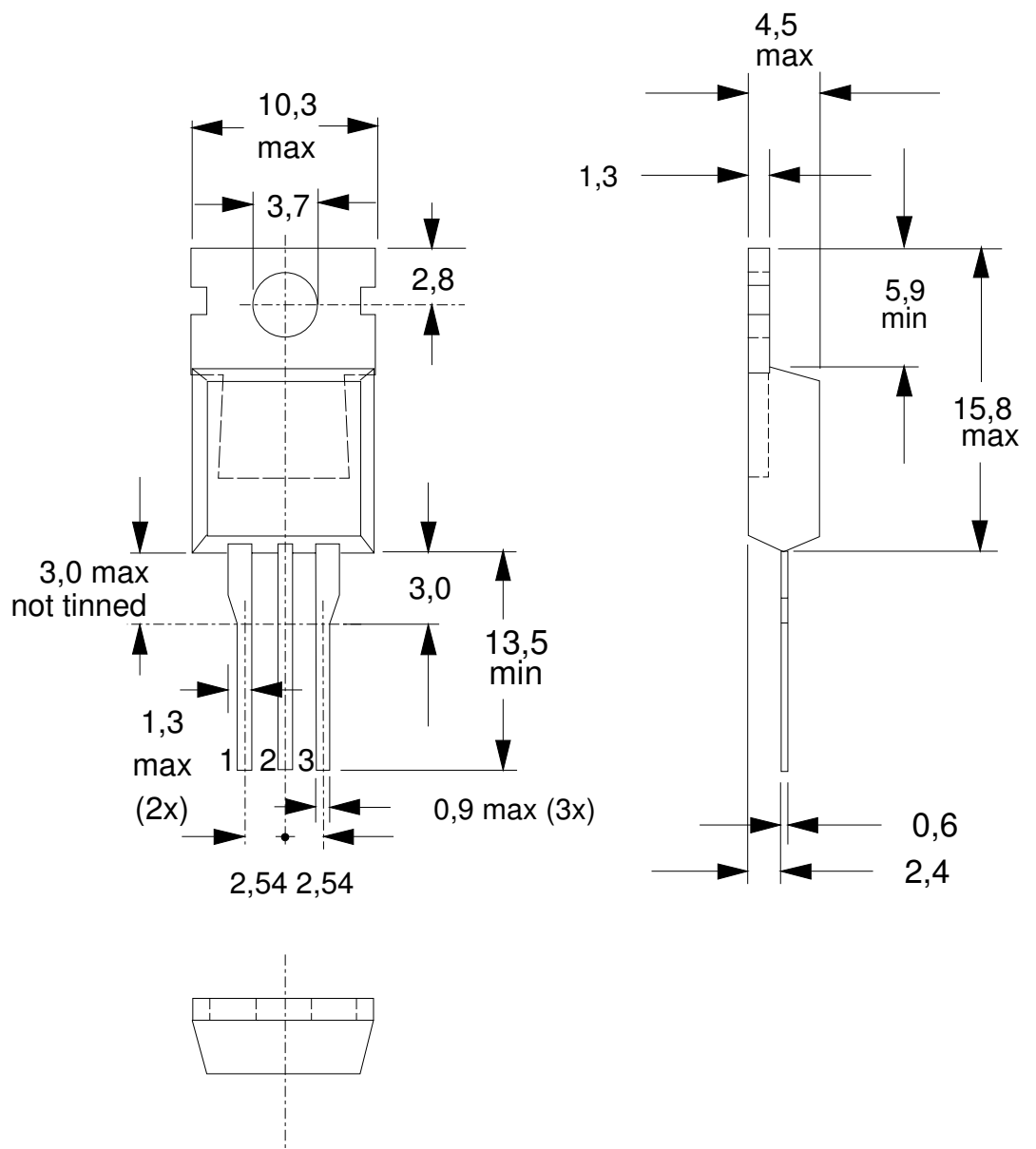


Fig.15. TO220AB; pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

Legal information

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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